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Science College	Date:
3rd Year Medical Physics	Time:

Q1/ Draw a "Light-Activated Circuit" using a photoresistor as the sensor element for light.



Q3/ Draw a circuit of op-amp "RC Relaxation Oscillators" and explain it briefly.

Q4/Explain the basic components of any "Voltage Regulators" circuit.

lc **Q5/** Given VCC = +15 V, VB = 5.6 V, R1 = $4.7 \text{ k}\Omega$, [−] Vc I_B $R2 = 3.3 \text{ k}\Omega$, and hFE = 100, find VE, IE, IB, IC, and VC. $V_B = 5.6 V$ V_E 0 *R*₂= 3.3 K I_E





+9V Q

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Q6/ Solve for the gain (Vout/Vin) of the circuit

below, then find the value of the voltage gain.

 $V_{\rm in}$

Q7/ If VGS,off = -4 V and IDSS = 12 mA, find the values of ID and gm and RDS when VGS=-2 V and when VGS=+1 V Assume that the JFET is in the active region.

Q8/ Draw and explain "ASTABLE MULTIVIBRATOR" transistor circuit.

Q9/ Solve for Vout in terms of Vin.

Q10/ Explain the basic configuration and function of "The 555 Timer IC".

Q11/ For the following "EMITTER-FOLLOWER AMPLIFIER" circuit, [Rload = $3k\Omega$, VCC = +20 V, β =100, f=100 Hz]. Find RE, R1, R2, Rin(base,dc), Rin(base,ac), C1, C2.



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Q12/ For the following "common-emitter amplifier" circuit, [voltage gain= -100, an f=100 Hz, and a quiescent current IQ = 1 mA, where β = 100 and VCC = 10 V]. Find RE, R1, R2, Rin(base,dc), Rin(base,ac), C1, C2.



Q13/Write 5 notes technical about "non-original phone chargers" available in the market.

Q14/ Draw the characteristic curve of JFET transistor.

Q15/ An *n*-channel depletion-type MOSFET has an *IDDS* = 10 mA and a *VGS*, off = -4 V. Find the values of *ID*, *gm*, and *RDS* when *VGS* = -2 V. Assume that the MOSFET is in the active region.

